

BAS85

FEATURES :

- * For general purpose applications.
- * This diode features low turn-on voltage.
- * This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges
- * This diode is also available in the DO-35 case with type designation BAT85.
- * Pb / RoHS Free

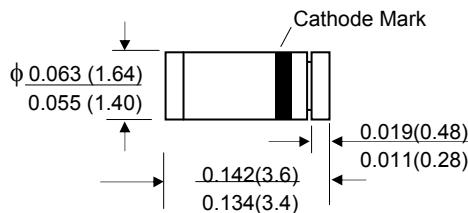
MECHANICAL DATA :

Case: MiniMELF Glass Case (SOD-80C)

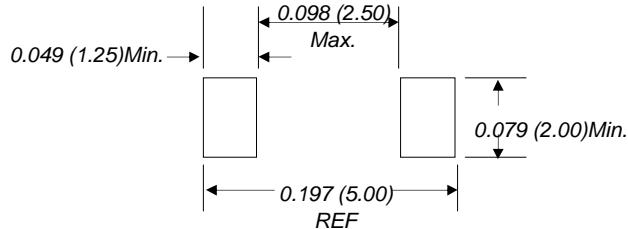
Weight: approx. 0.05g

SCHOTTKY BARRIER DIODE

MiniMELF (SOD-80C)



Mounting Pad Layout



Dimensions in inches and (millimeters)

Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Continuous Reverse Voltage	V _R	30	V
Continuous Forward Current	I _F	200 ⁽¹⁾	mA
Peak Forward Current	I _{FM}	300 ⁽¹⁾	mA
Forward Surge Current	I _{FSM}	600 ⁽¹⁾	mA
Power Dissipation (Infinite Heatsink)	P _D	200 ⁽¹⁾	mW
Thermal Resistance Junction to Ambient Air	R _{0JA}	430 ⁽¹⁾	°C/W
Junction Temperature	T _J	125	°C
Storage temperature range	T _{STG}	-55 to + 150	°C

Note: (1) Valid provided that electrodes are kept at ambient temperature.

Electrical Characteristics (T_J = 25 °C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V _{(BR)R}	I _R = 10 µA (pulsed)	30	-	-	V
Reverse Current	I _R	V _R = 25 V	-	0.2	2.0	µA
Forward Voltage Pulse Test tp <300µs , δ <2%	V _F	I _F = 1mA	-	-	0.32	V
		I _F = 10mA	-	-	0.40	
		I _F = 30mA	-	0.5	-	
		I _F = 100mA	-	-	0.80	
Diode Capacitance	C _d	V _R = 1V, f = 1MHz	-	-	10	pF
Reverse Recovery Time	T _{rr}	I _F = 10mA to I _R = 10mA , measured at I _R = 1mA	-	-	5	ns